# 4V Drive Nch MOS FET **RHK003N06**

#### ●Structure

Silicon N-channel MOS FET

### ● Features

- 1) Low On-resistance.
- 2) 4V drive.

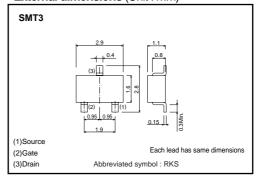
### Applications

Switching

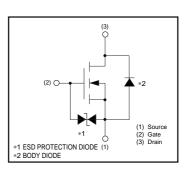
# ●Packaging specifications and hFE

	Package	Taping
Туре	Code	T146
	Basic ordering unit (pieces)	3000
RHK003N06	0	

# ●External dimensions (Unit : mm)



#### •Inner circuit



## ● Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit
Drain-source voltage		VDSS	60	V
Gate-source voltage		Vgss	±20	V
Droin augrent	Continuous	ID	±300	mA
Drain current	Pulsed	IDP *1	±1.2	Α
Source current (Body diode)	Continuous	Is	200	mA
	Pulsed	Isp *1	800	mA
Total power dissipation		Pp *2	200	mW
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	-55 to +150	°C

### ●Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	Rth(ch-a)*	625	°C/W

<sup>\*</sup> Each terminal mounted on a recommended land

<sup>\*1</sup> Pw≤10µs, Duty cycle≤1% \*2 Each terminal mounted on a recommended land

# ●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	Igss	-	_	±10	μΑ	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V
Drain-source breakdown voltage	V <sub>(BR) DSS</sub>	60	_	_	V	I <sub>D</sub> = 1mA, V <sub>GS</sub> =0V
Zero gate voltage drain current	IDSS	_	_	1	μΑ	V <sub>DS</sub> = 60V, V <sub>GS</sub> =0V
Gate threshold voltage	V <sub>GS (th)</sub>	1.0	_	2.5	V	V <sub>DS</sub> = 10V, I <sub>D</sub> = 1mA
Static drain-source on-state	D*	_	0.7	1.0	Ω	I <sub>D</sub> = 300mA, V <sub>GS</sub> = 10V
resistance	R <sub>DS</sub> (on)*	_	1.1	1.5	Ω	I <sub>D</sub> = 300mA, V <sub>GS</sub> = 4V
Forward transfer admittance	Y <sub>fs</sub>   *	0.2	_	_	S	V <sub>DS</sub> = 10V, I <sub>D</sub> = 300mA
Input capacitance	Ciss	_	33	_	pF	V <sub>DS</sub> = 10V
Output capacitance	Coss	_	14	_	pF	V <sub>GS</sub> =0V
Reverse transfer capacitance	Crss	_	9	_	pF	f=1MHz
Turn-on delay time	t <sub>d (on)</sub> *	-	6	_	ns	Vpp≒ 30V
Rise time	tr *	_	5	_	ns	I <sub>D</sub> = 150mA   V <sub>G</sub> s= 10V
Turn-off delay time	t <sub>d (off)</sub> *	-	13	_	ns	VGS= 10V   RL=200Ω
Fall time	t <sub>f</sub> *	_	80	_	ns	R <sub>G</sub> =10Ω
Total gate charge	Qg *	_	3	6	nC	V <sub>DD</sub> ≒30V
Gate-source charge	Qgs *		0.6	_	nC	Vgs= 10V
Gate-drain charge	Q <sub>gd</sub> *	_	0.5	_	nC	Ip= 300mA

\*Pulsed

# ●Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsp*	_	_	1.2	V	Is= 300mA, V <sub>GS</sub> =0V

\*Pulsed

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